

TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (L^2 - π -MOSV)

2SK2882

Chopper Regulator, DC-DC Converter and Motor Drive Applications

Unit: mm

- 4-V gate drive
- Low drain-source ON resistance: $R_{DS(ON)} = 0.08 \Omega$ (typ.)
- High forward transfer admittance: $|Y_{fs}| = 17 S$ (typ.)
- Low leakage current: $I_{DSS} = 100 \mu A$ (max) ($V_{DS} = 150 V$)
- Enhancement mode: $V_{th} = 0.8 \sim 2.0 V$ ($V_{DS} = 10 V$, $I_D = 1 mA$)

Absolute Maximum Ratings ($T_a = 25^\circ C$)

Characteristics	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	150	V
Drain-gate voltage ($R_{GS} = 20 k\Omega$)	V_{DGR}	150	V
Gate-source voltage	V_{GSS}	± 20	V
Drain current	DC (Note 1)	I_D	A
	Pulse (Note 1)	I_{DP}	
Drain power dissipation ($T_c = 25^\circ C$)	P_D	45	W
Single pulse avalanche energy (Note 2)	E_{AS}	176	mJ
Avalanche current	I_{AR}	18	A
Repetitive avalanche energy (Note 3)	E_{AR}	4.5	mJ
Channel temperature	T_{ch}	150	$^\circ C$
Storage temperature range	T_{stg}	$-55 \sim 150$	$^\circ C$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

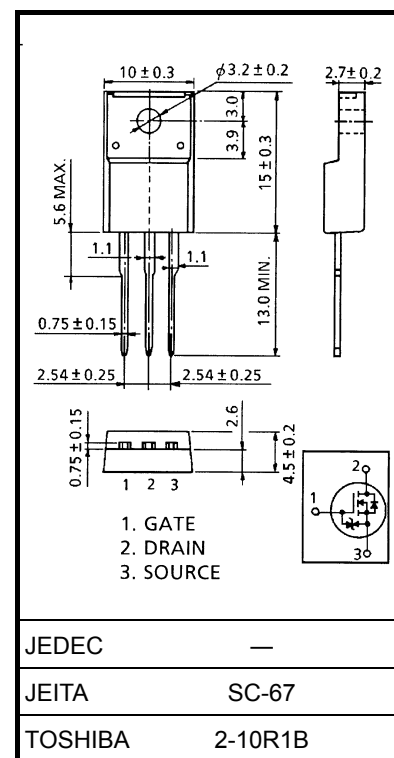
Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	$R_{th(ch-c)}$	2.78	$^\circ C/W$
Thermal resistance, channel to ambient	$R_{th(ch-a)}$	62.5	$^\circ C/W$

Note 1: Ensure that the channel temperature does not exceed $150^\circ C$.

Note 2: $V_{DD} = 50 V$, $T_{ch} = 25^\circ C$ (initial), $L = 0.8 mH$, $R_G = 25 \Omega$, $I_{AR} = 18 A$

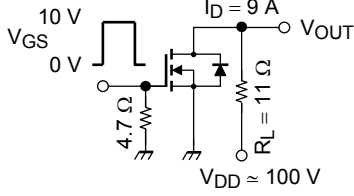
Note 3: Repetitive rating: pulse width limited by maximum junction temperature

This transistor is an electrostatic-sensitive device. Please handle with caution.



Weight: 1.9 g (typ.)

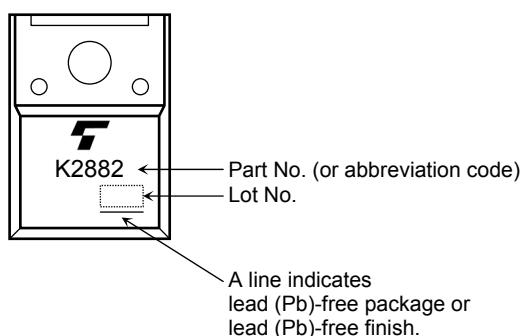
Electrical Characteristics (Ta = 25°C)

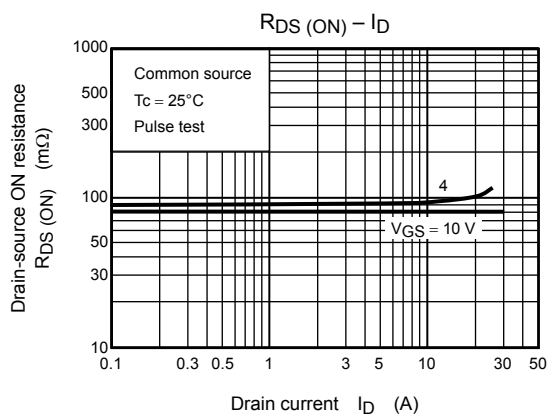
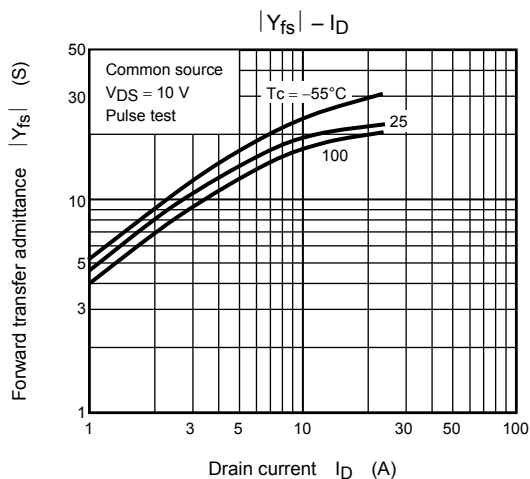
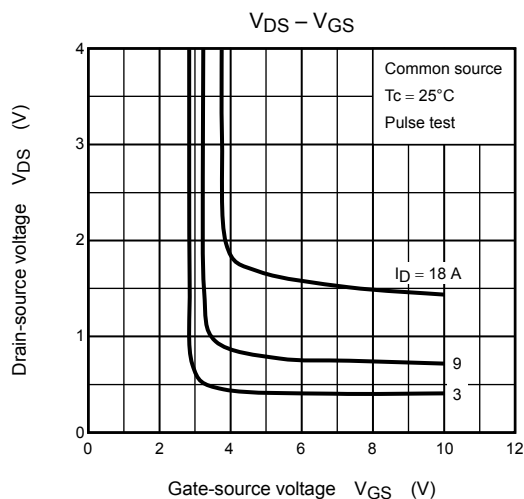
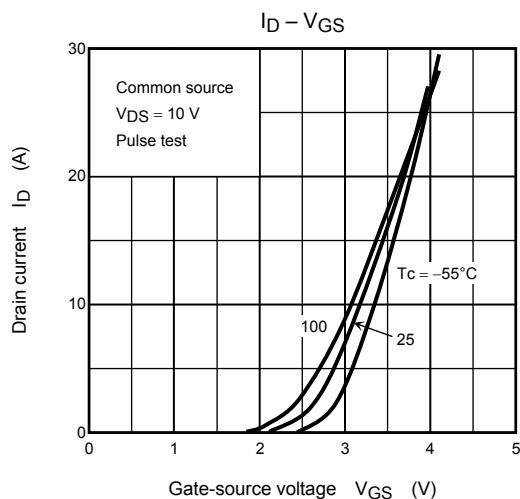
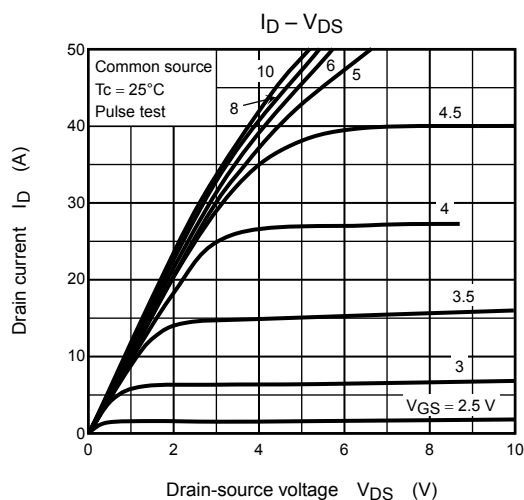
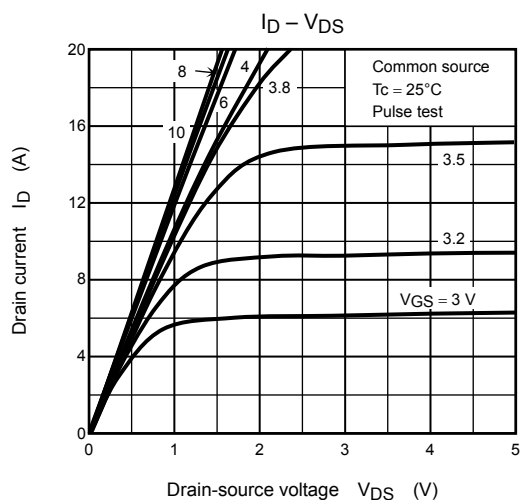
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0 \text{ V}$	—	—	± 10	μA
Drain cut-off current		I_{DSS}	$V_{DS} = 150 \text{ V}$, $V_{GS} = 0 \text{ V}$	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR) DSS}$	$I_D = 10 \text{ mA}$, $V_{GS} = 0 \text{ V}$	150	—	—	V
Gate threshold voltage		V_{th}	$V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$	0.8	—	2.0	V
Drain-source ON resistance		$R_{DS(ON)}$	$V_{GS} = 4 \text{ V}$, $I_D = 9 \text{ A}$	—	0.09	0.18	Ω
			$V_{GS} = 10 \text{ V}$, $I_D = 9 \text{ A}$	—	0.08	0.12	
Forward transfer admittance		$ Y_{fs} $	$V_{DS} = 10 \text{ V}$, $I_D = 9 \text{ A}$	10	17	—	S
Input capacitance		C_{iss}	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	—	1380	—	pF
Reverse transfer capacitance		C_{rss}		—	200	—	pF
Output capacitance		C_{oss}		—	610	—	pF
Switching time	Rise time	t_r		—	12	—	ns
	Turn-on time	t_{on}		—	24	—	
	Fall time	t_f		—	56	—	
	Turn-off time	t_{off}		—	130	—	
Total gate charge (gate-source plus gate-drain)		Q_g	$V_{DD} \approx 120 \text{ V}$, $V_{GS} = 10 \text{ V}$, $I_D = 18 \text{ A}$	—	57	—	nC
Gate-source charge		Q_{gs}		—	43	—	nC
Gate-drain ("miller") charge		Q_{gd}		—	14	—	nC

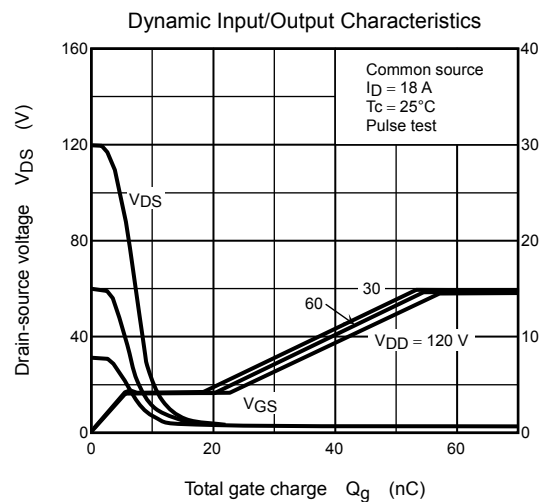
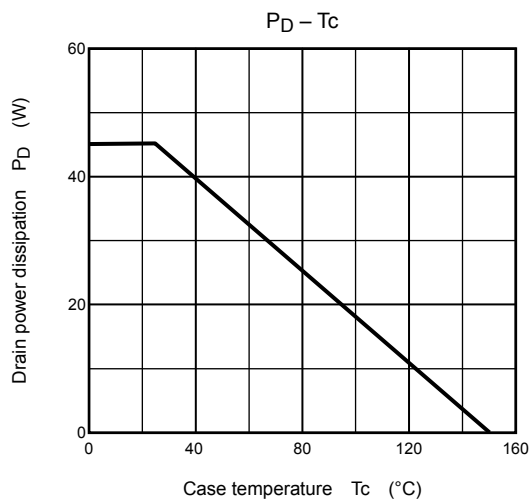
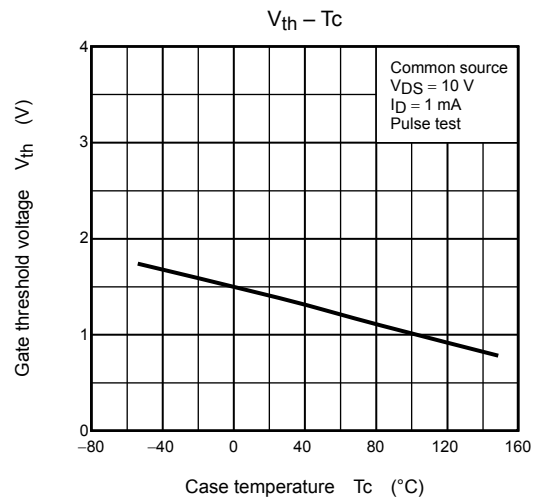
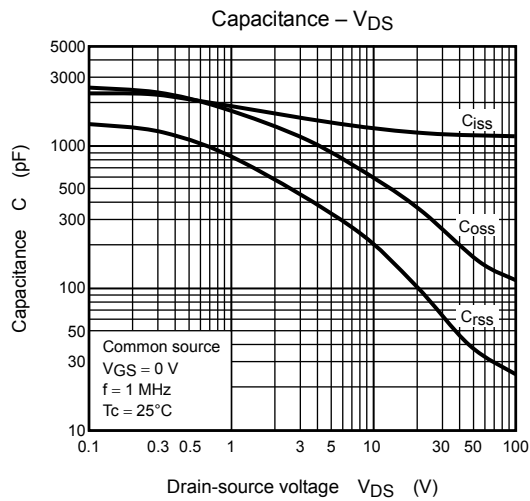
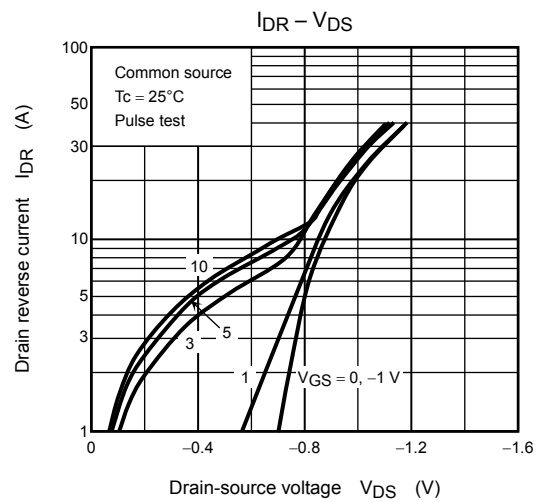
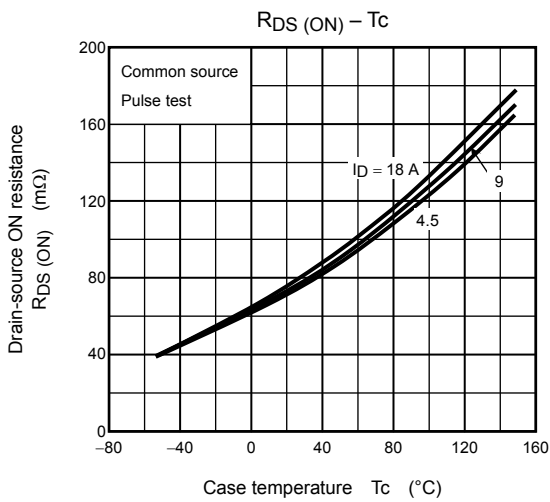
Source-Drain Ratings and Characteristics (Ta = 25°C)

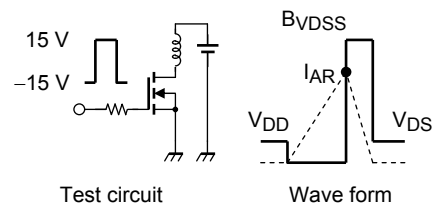
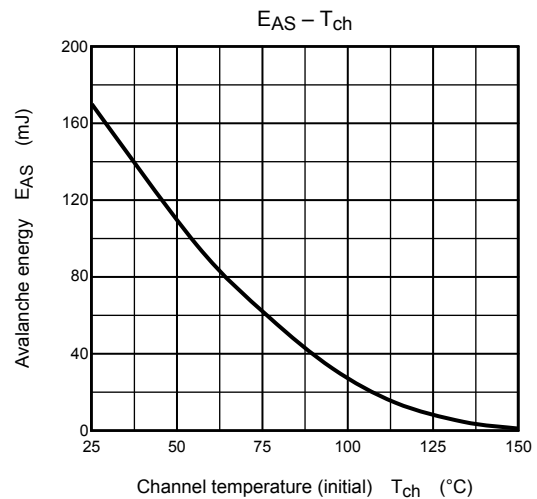
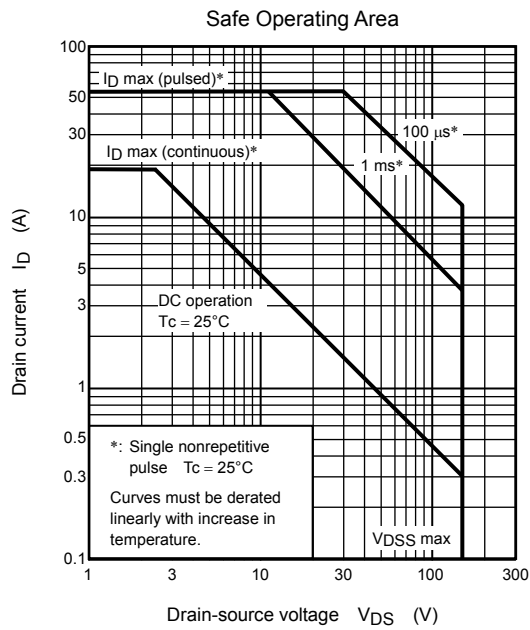
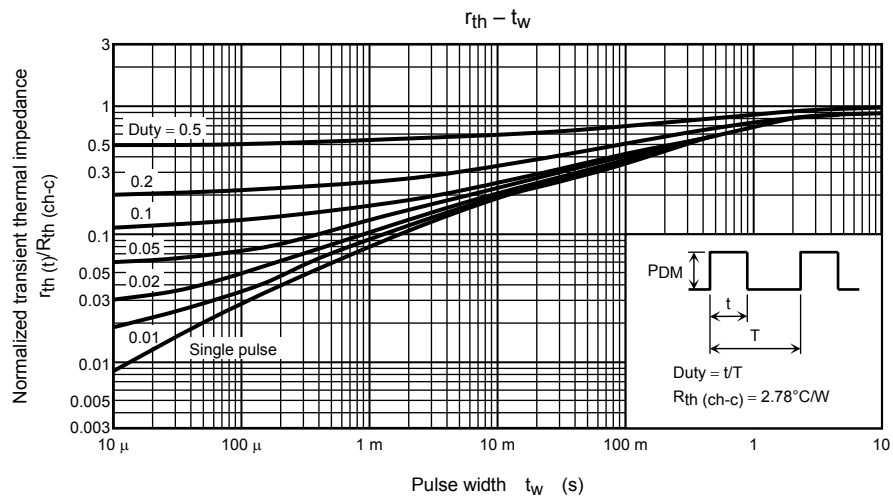
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Continuous drain reverse current (Note 1)	I_{DR}	—	—	—	18	A
Pulse drain reverse current (Note 1)	I_{DRP}	—	—	—	54	A
Forward voltage (diode)	V_{DSF}	$I_{DR} = 18 \text{ A}$, $V_{GS} = 0 \text{ V}$	—	—	−1.7	V
Reverse recovery time	t_{rr}	$I_{DR} = 18 \text{ A}$, $V_{GS} = 0 \text{ V}$	—	185	—	ns
Reverse recovery charge	Q_{rr}	$dI_{DR}/dt = 100 \text{ A}/\mu\text{s}$	—	1.3	—	μC

Marking









$$R_G = 25 \Omega$$

$$V_{DD} = 50 V, L = 0.8 mH$$

$$E_{AS} = \frac{1}{2} \cdot L \cdot I^2 \cdot \left(\frac{B_{VDSS}}{B_{VDSS} - V_{DD}} \right)$$

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